

# Muhammad Luqman Nur Hakim Kamarudin

Centre for Electrical Engineering Studies, Universiti Teknologi MARA, Cawangan Pulau Pinang, 13500

## Alhan Farhanah Abd Rahim

Centre for Electrical Engineering Studies, Universiti Teknologi MARA, Cawangan Pulau Pinang, 13500

Nurul Syuhadah Mohd Razali

Centre for Electrical Engineering Studies, Universiti Teknologi MARA, Cawangan Pulau Pinang, 13500

Rosfariza Radzali

Centre for Electrical Engineering Studies, Universiti Teknologi MARA, Cawangan Pulau Pinang, 13500

# Ainorkhilah Mahmood

Department of Applied Sciences, Universiti Teknologi MARA, Cawangan Pulau Pinang, 13500 Permata

#### Irni Hamiza Hamzah

Centre for Electrical Engineering Studies, Universiti Teknologi MARA, Cawangan Pulau Pinang, 13500

## Mohaiyedin Idris

Centre for Electrical Engineering Studies, Universiti Teknologi MARA, Cawangan Pulau Pinang, 13500

## Mohamed Fauzi Packeer Mohamed

School of Electrical and Electronic Engineering, Engineering Campus, Universiti Sains Malaysia, 14300

#### Abstract

Insufficiently high dopinguin polysilicon gates of metal 4 paride 0s2 miconductor field effect transistor (11/) (08)



#### Keyword: Scaled NMOS, SILVACO TCAD tools, Gate Geometric Effect, Polysilicor

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